P-Channel Enhancement Mode Power MOSFET

Description

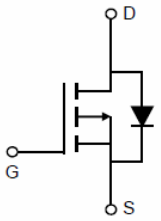
The HM2309APR uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge .This device is well suited for use as a load switch or in PWM applications.

General Features

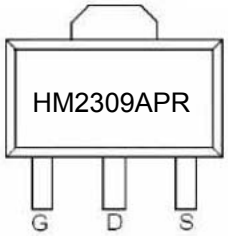
- V_{DS} =-60V,I_D =-5A
  $R_{DS(ON)}$ <120mΩ @ V_{GS}=-10V
  $R_{DS(ON)}$ <170mΩ @ V_{GS}=-4.5V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

- Load switch
- PWM application



Schematic diagram



SOT-89 -3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM2309APR	HM2309APR	SOT-89-3L	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	-5	A
Pulsed Drain Current	I_{DM}	-15	A
Maximum Power Dissipation	P_D	1.5	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient(Note 2)	$R_{\theta JA}$	83.3	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

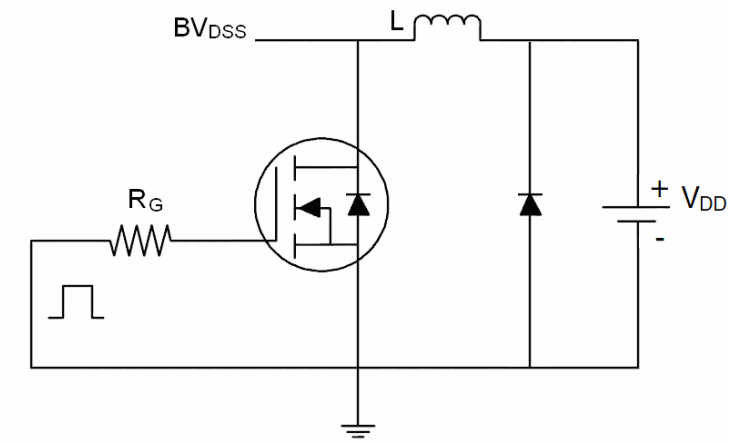
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-60V,V_{GS}=0V	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-1.5	-2.2	-3.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-5A	-	106	120	mΩ
		V_{GS}=-4.5V, I_D=-3A	-	135	170	mΩ
Forward Transconductance	g_{FS}	V_{DS}=-5V,I_D=-5A	-	10	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=-30V,V_{GS}=0V, F=1.0MHz	-	930	-	PF
Output Capacitance	C_{oss}		-	85	-	PF
Reverse Transfer Capacitance	C_{rss}		-	35	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-30V, R_L=7.5Ω, V_{GS}=-10V,R_G=3Ω	-	8	-	nS
Turn-on Rise Time	t_r		-	4	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	32	-	nS
Turn-Off Fall Time	t_f		-	7	-	nS
Total Gate Charge	Q_g	V_{DS}=-30,I_D=-5A, V_{GS}=-10V	-	25	-	nC
Gate-Source Charge	Q_{gs}		-	3	-	nC
Gate-Drain Charge	Q_{gd}		-	7	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=-5A	-		-1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-5	A
Reverse Recovery Time	t_{rr}	T_J = 25°C, I_F =- 5A di/dt = -100A/μs (Note3)	-	25		nS
Reverse Recovery Charge	Qrr		-	31		nC

Notes:

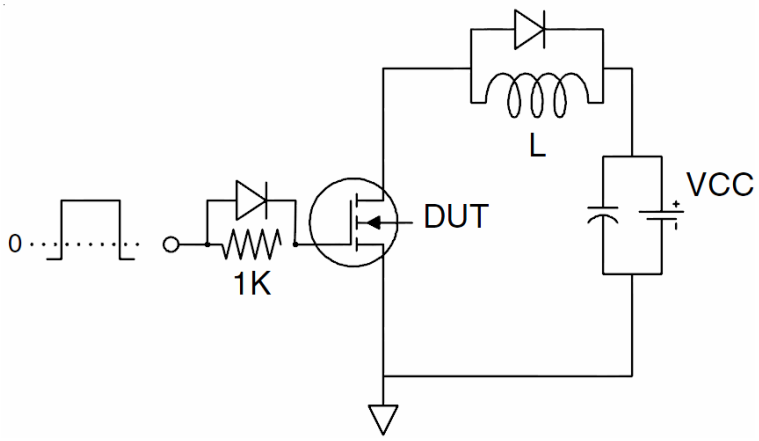
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Test Circuit

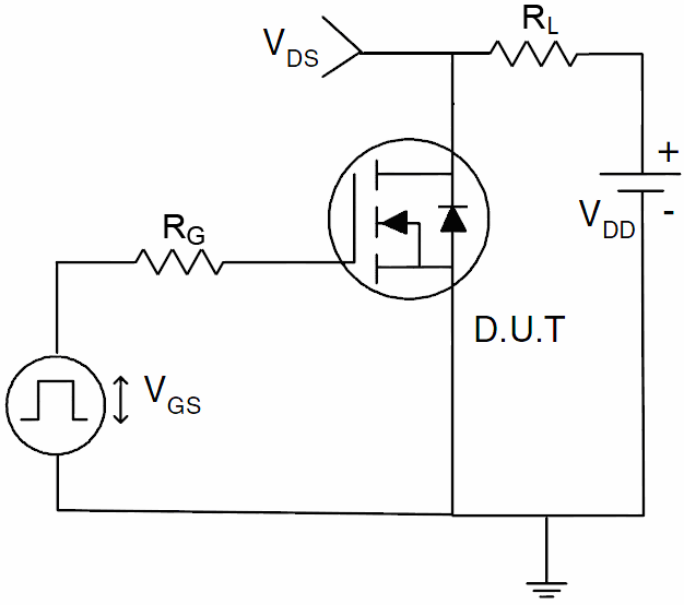
1）E_{AS} test Circuit



2）Gate charge test Circuit



3）Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

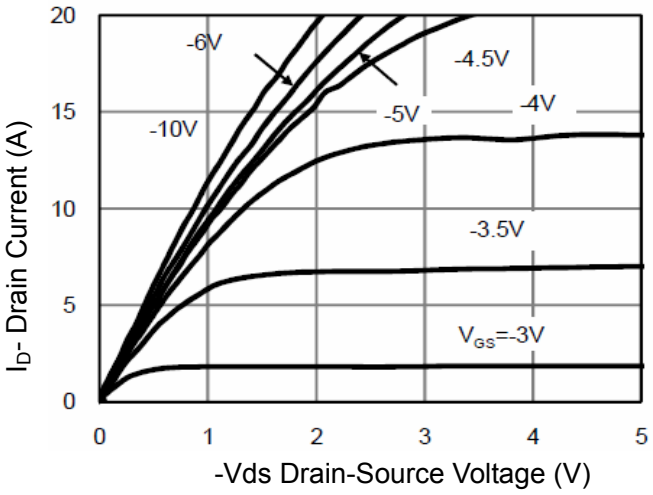


Figure 1 Output Characteristics

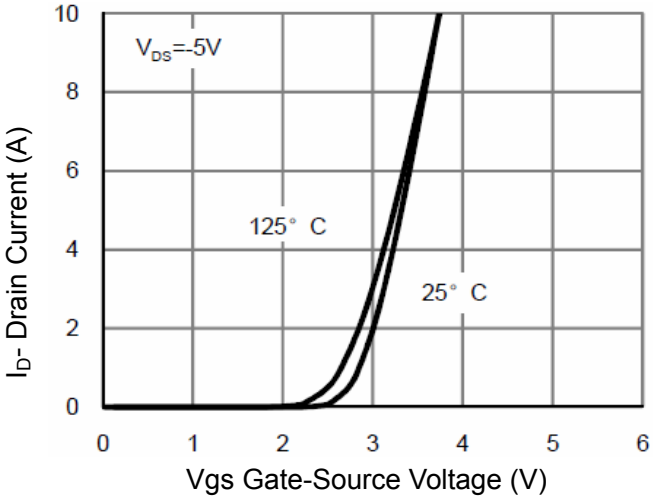


Figure 2 Transfer Characteristics

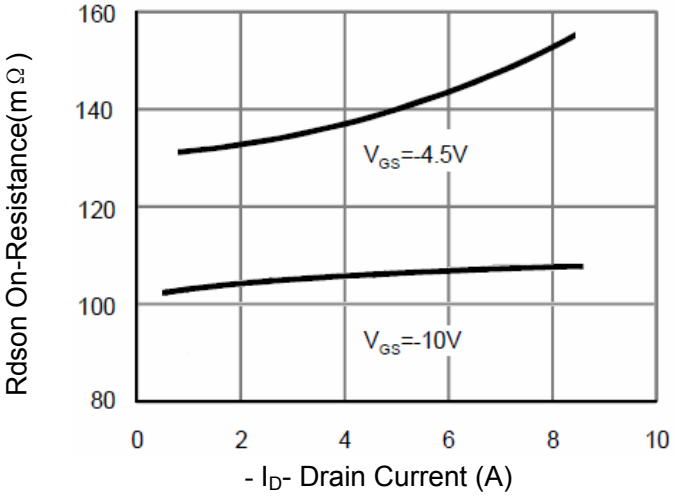


Figure 3 Rdson- Drain Current

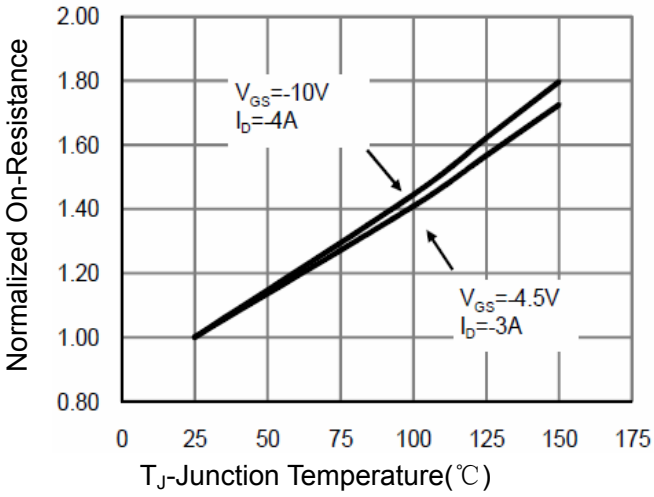


Figure 4 Rdson-Junction Temperature

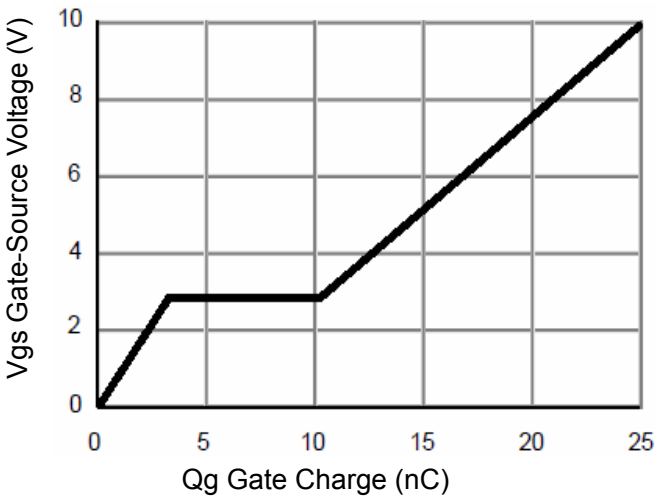


Figure 5 Gate Charge

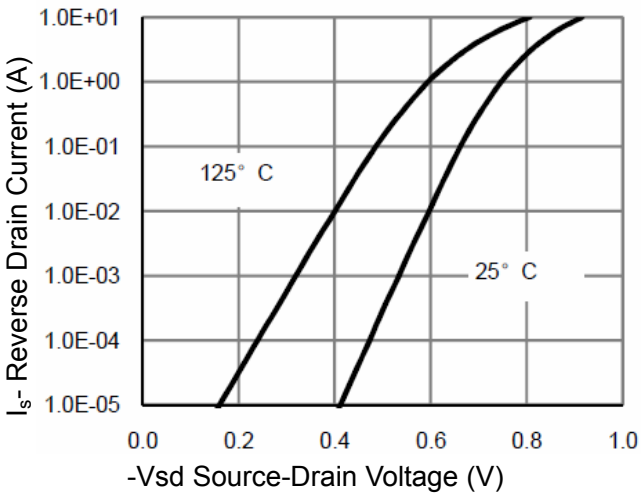


Figure 6 Source- Drain Diode Forward

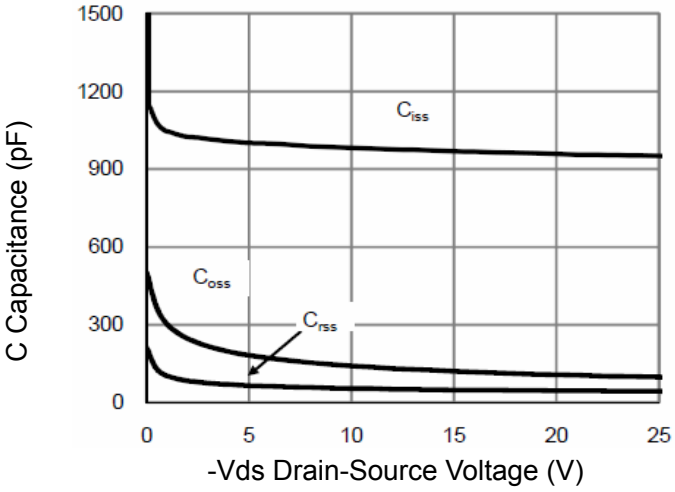


Figure 7 Capacitance vs Vds

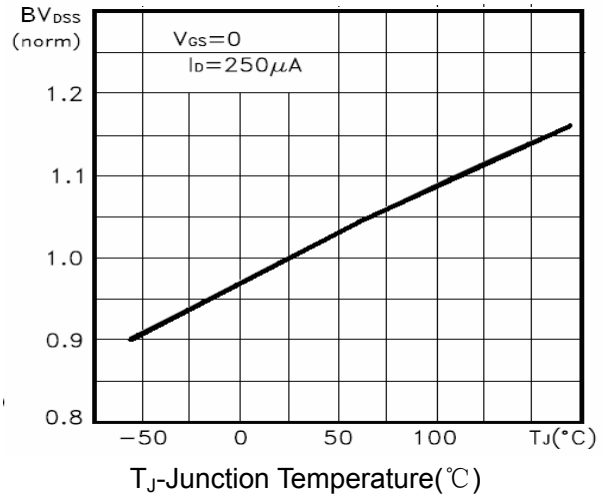


Figure 9 BV_{DSS} vs Junction Temperature

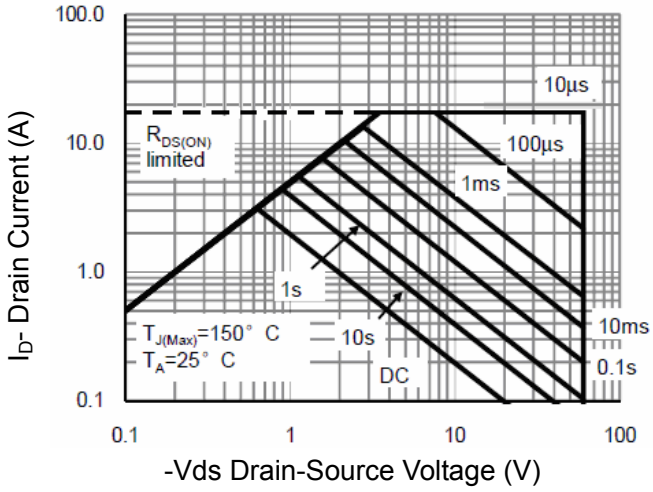


Figure 8 Safe Operation Area

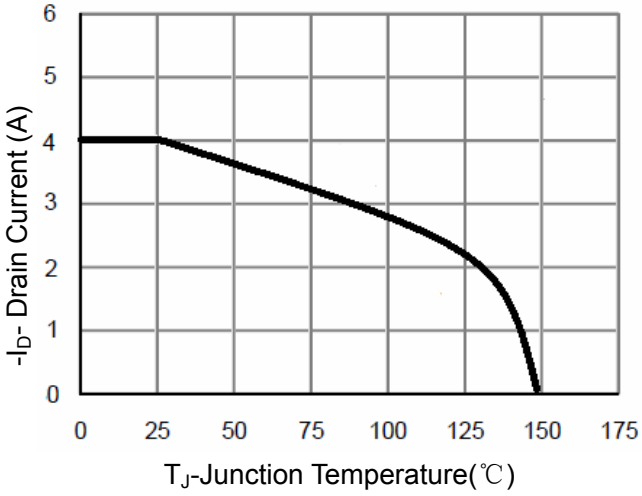


Figure 10 ID Current De-rating

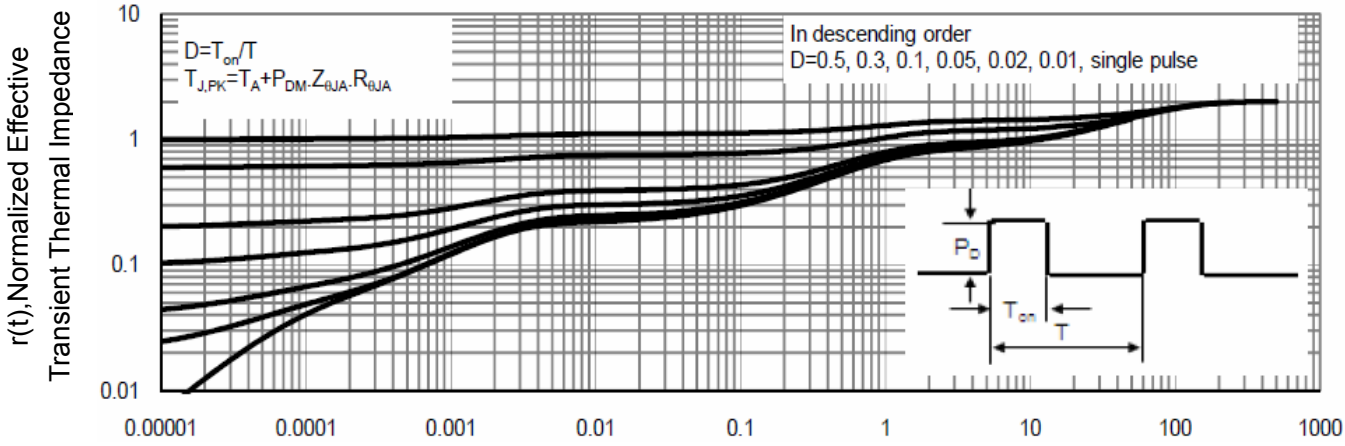
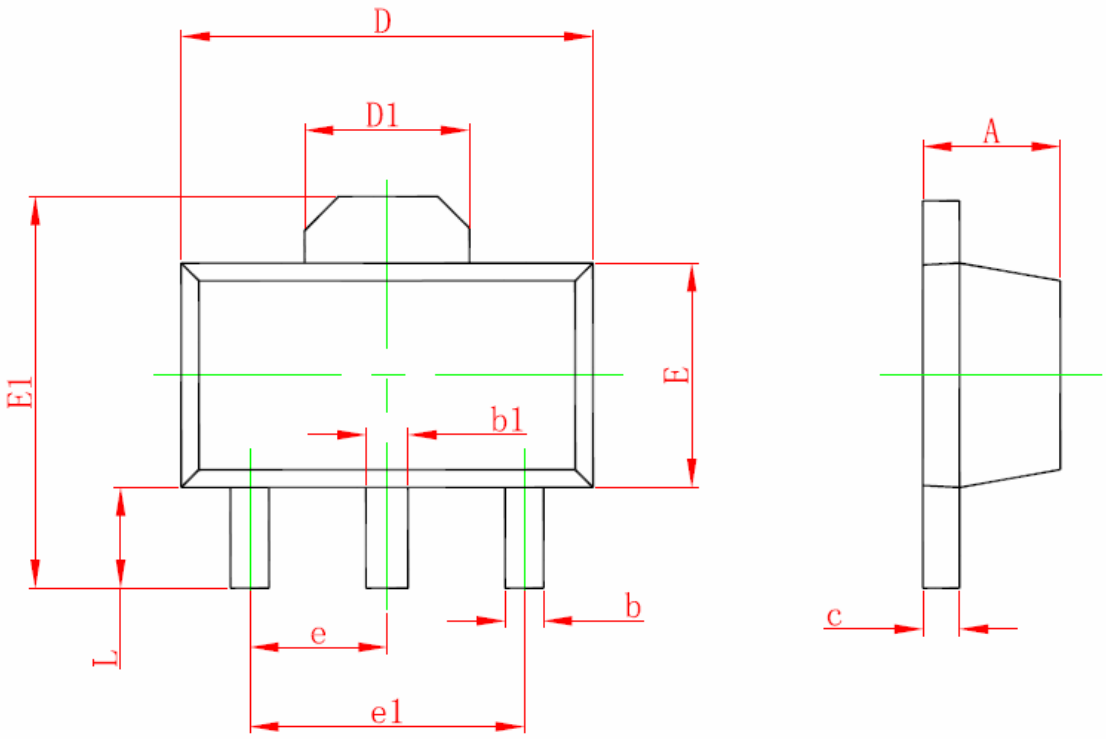


Figure 11 Normalized Maximum Transient Thermal Impedance

SOT-89-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047

Notes

1. All dimensions are in millimeters.
2. Tolerance ±0.10mm (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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